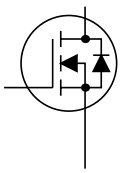
Part Number: 5.IRFP260NPBF
Sample ID: 5A-1
Description: sample
Operator: YM
Measurement Instrument: B1506AH51_MY59200135



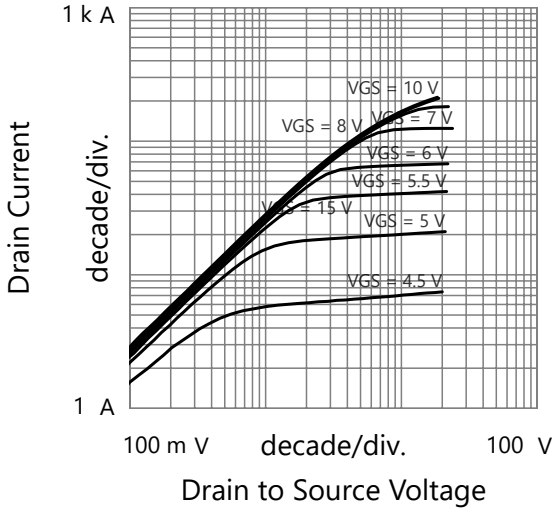
Maximum Ratings

Symbol	*Parameter*	*Test Conditions*	*Value*	*Unit*	*Note*
VDSS	Drain to Source Voltage	Tj=-55 °C to 175 °C	200	V	
VGSS	Gate to Source Voltage	Conitnuous	-20 to 20	V	
IDM	Pulsed Drain Current	Tc=25 °C	200	A	
ISM	Pulsed Body Diode Current	Tc=25 °C	200	A	

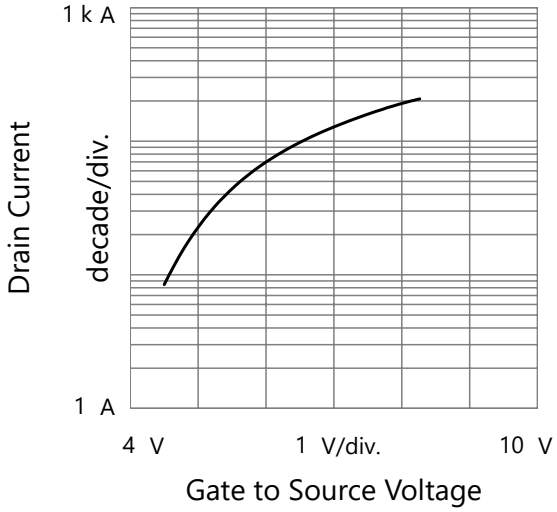
Characteristics Parameters

Symbol	*Parameter*	*Test Conditions*	*Min.*	*Act.*	*Max.*	*Unit*	*Note*
BVDSS	Drain to Source Breakdown Voltage	VGS=0 V, ID=250 µA	200	219		V	
IDSS	Drain Leakage Current	VDS=200 V, VGS=0 V		1.38 n	25 µ	A	
IGSS	Gate Leakage Current	VGS=20 V, VDS=0 V		37.6 p	100 n	A	
IGSS(-)	Gate Leakage Current (-)	VGS=-20 V, VDS=0 V	-100 n	-43.8 p		A	
VGS(th)	Gate to Source Threshold Voltage (VDS=VGS)	ID=250 µA	2	2.88	4	V	
RDS(on)	Drain to Source On Resistance	VGS=10 V, ID=28 A, PulseWidth=200 µs		36.2 m	40 m	ohm	
VSD	Body Diode Forward Voltage	VGS=0 V, IS=28 A, PulseWidth=200 µs		889 m	1.3	V	
Rg	Gate Resistance	VGS=0 V, f=1 MHz		NaN		ohm	Not specified
Ciss	Input Capacitance	VGS=0 V, VDS=25 V, f=100 kHz		4 n		F	Typ. 4057 pF
Coss	Output Capacitance	VGS=0 V, VDS=25 V, f=100 kHz		586 p		F	Typ. 603 pF
Crss	Reverse Transfer Capacitance	VGS=0 V, VDS=25 V, f=100 kHz		147 p		F	Typ. 161pF
Qg	Total Gate Charge	Vgs(on)=10 V, Vgs(off)=0 V, Vds=160 V, Id=28 A	0	113 n	234 n	C	
Qgs	Gate to Source Charge	Vgs(on)=10 V, Vgs(off)=0 V, Vds=160 V, Id=28 A		19.2 n	38 n	C	
Qgd	Gate to Drain Charge	Vgs(on)=10 V, Vgs(off)=0 V, Vds=160 V, Id=28 A		53.7 n	110 n	C	

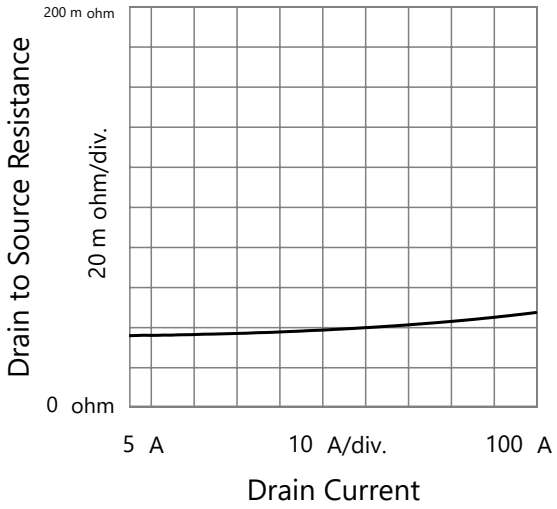
Output Characteristics(Pulse width:40us)



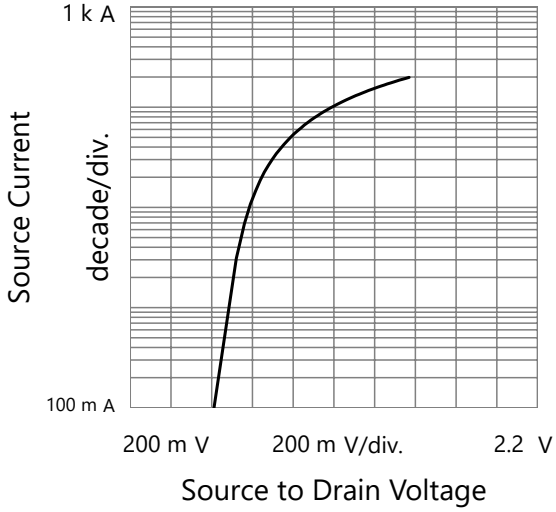
Transfer Characteristics(Vds:35 V @200A)



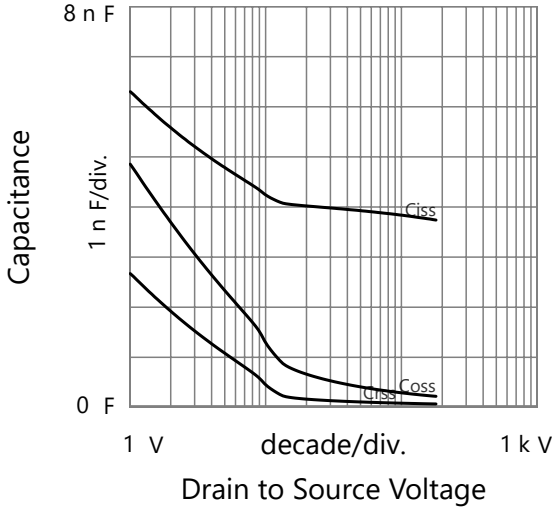
Drain to Source Resistance vs. Drain Current



Body Diode Forward Characteristics



Capacitances



Gate Charge (Vds:160V, Id:28A)